

Notice of References Cited	Application/Control No. 10/785,005	Applicant(s)/Patent Under Reexamination FUJITA, SHIGERU	
	Examiner Thao X. Le	Art Unit 2814	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2002/0190302	12-2002	Bojarczuk et al.	257/310
*	B	US-6,436,848	08-2002	Ramkumar, Krishnaswamy	438/777
*	C	US-6,900,122	05-2005	Ahn et al.	438/635
*	D	US-6,563,182	05-2003	Horikawa, Tsuyoshi	257/405
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	H.J. OSten, et al., High-K Dielectrics With Ultra-low Leakage Current Based on Praseodymium Oxide, 2000, IEEE, 653-656.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.